

**REMARKS**

Claims 1-37 remain pending in the application. This supplemental response corrects a minor typographical error which applicant recently discovered in the application.

Respectfully submitted,

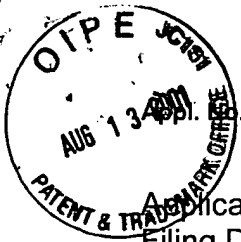
Dated: \_\_\_\_\_

8/16/01

By: \_\_\_\_\_

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Reg. No. 38,533

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09/488,973

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Application Serial No. ....09/488,973  
Filing Date .....AUG 15 2001..... January 20, 2000  
Inventor..... Parfeniuk et al.  
Assignee..... TECHNOLOGY CENTER 2800..... Honeywell International Inc.  
Group Art Unit.....2823  
Examiner .....D. Collins  
Attorney's Docket No. ....HO57-002  
Title: Methods of Bonding First and Second Masses to One Another, and Methods of  
Bonding Physical Vapor Deposition Target Materials to Backing Plate Materials

VERSION WITH MARKINGS TO SHOW CHANGES MADE IN ACCOMPANYING  
SUPPLEMENTAL RESPONSE

In the Specification

The replacement specification paragraph incorporates the following amendments.

Underlines indicate insertions and ~~strikeouts~~ indicate deletions. The paragraph beginning  
at lines 12-23 on page 13 has been amended as follows:

In addition to the strong bond formed between target 50 and backing plate 60 of  
assembly 70, a grain size of target 50 is preferably below 100 microns, more preferably  
from about 30 to less than 100 microns, and more preferably below about 50 microns after  
the diffusion bonding. Specifically, a predominate portion (i.e., more than 50%) of the  
grains in target 50 will preferably have a maximum dimension of less than 100 microns,  
more preferably from about 30 microns to less than 100 microns, and more preferably less  
than about 50 microns. In particular embodiments, an entirety of the grains in target 50  
have a maximum dimension of less than 100 microns, more preferably from about 30  
microns to less than 100 microns, and more preferably less than about 50 microns.

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